

SOI SEMICONDUCTOR DEVICE WITH REDUCED TOPOGRAPHY ABOVE A SUBSTRATE WINDOW AREA

ABSTRACT

5 In sophisticated SOI devices, circuit elements, such as substrate diodes, may be formed in the crystalline substrate material on the basis of a substrate window, wherein the pronounced surface topography may be compensated for or at least reduced by performing additional planarization processes, such as the deposition of a planarization material, and a subsequent etch process when forming the contact level of the semiconductor device.

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Figure 2a